NSN 5961-01-291-6407

Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-291-6407 **Inclosure Material:** Metal and glass **Overall Length:** Between 0.155 inches and 0.185 inches **Terminal Length:** 0.500 inches **Overall Diameter:** Between 0.335 inches and 0.370 inches **Mounting Method:** Terminal **Terminal Circle Diameter:** Between 0.190 inches and 0.210 inches **Features Provided:** Electrostatic sensitive **Semiconductor Material:** Silicon **Voltage Rating In Volts Per Characteristic:** 300.0 breakdown voltage, dc and 475.0 breakdown voltage, dc **Current Rating Per Characteristic:** 5.00 milliamperes source cutoff current preset **Maximum Operating Tempurature Per Measurement Point:** 70.0 degrees celsius ambient air **Special Features:** Field force effect type: electrostatic charge **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** Yes - demil/mli

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